# BAS21SLT1G, NSVBAS21SLT1G

# **Dual Series High Voltage Switching Diode**

# Features

- Moisture Sensitivity Level: 1
- ESD Rating Human Body Model: Class 1 – Machine Model: Class B
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

# MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V <sub>R</sub>	250	Vdc
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	250	Vdc
Peak Forward Current	١ <sub>F</sub>	225	mAdc
Peak Forward Surge Current	I <sub>FM(surge)</sub>	625	mAdc

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$	P <sub>D</sub>	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^{\circ}C$	P <sub>D</sub>	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	– 55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

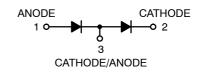
1. FR–5 = 1.0  $\times$  0.75  $\times$  0.062 in.

2. Alumina = 0.4  $\times$  0.3  $\times$  0.024 in. 99.5% alumina.



# **ON Semiconductor®**

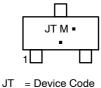
http://onsemi.com

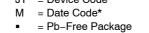




CASE 318 STYLE 11

## MARKING DIAGRAM





(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

## **ORDERING INFORMATION**

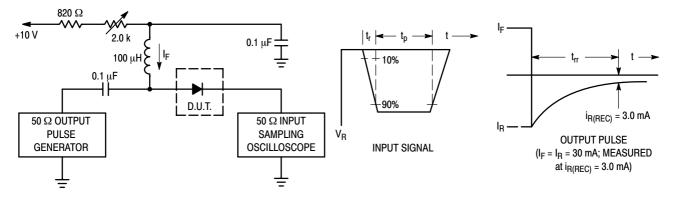
Device	Package	Shipping <sup>†</sup>
BAS21SLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBAS21SLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

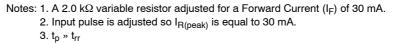
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# BAS21SLT1G, NSVBAS21SLT1G

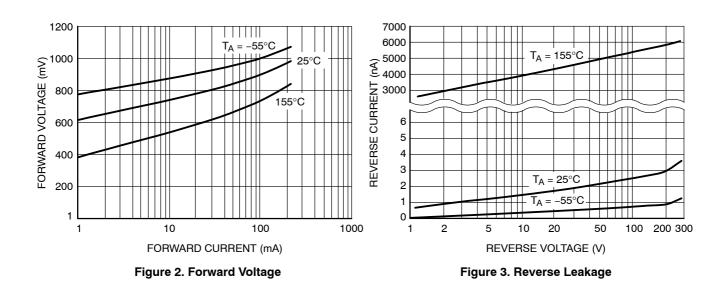
# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Reverse Voltage Leakage Current (V <sub>R</sub> = 200 Vdc) (V <sub>R</sub> = 200 Vdc, T <sub>J</sub> = 150°C)	I <sub>R</sub>		0.1 100	μAdc		
Reverse Breakdown Voltage (I <sub>BR</sub> = 100 μAdc)	V <sub>(BR)</sub>	250	-	Vdc		
Forward Voltage ( $I_F = 100 \text{ mAdc}$ ) ( $I_F = 200 \text{ mAdc}$ )	V <sub>F</sub>		1000 1250	mV		
Diode Capacitance (V <sub>R</sub> = 0, f = 1.0 MHz)	CD	-	5.0	pF		
Reverse Recovery Time ( $I_F = I_R = 30 \text{ mAdc}, R_L = 100 \Omega$ )	t <sub>rr</sub>	-	50	ns		





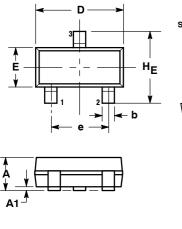


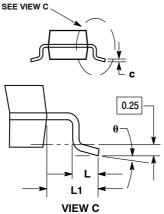


# BAS21SLT1G, NSVBAS21SLT1G

### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AP





NOTES:

STYLE 11:

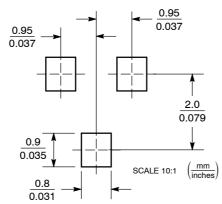
PIN 1. ANODE 2. CATHODE

CATHODE-ANODE

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
с	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

**SOLDERING FOOTPRINT\*** 



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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